

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

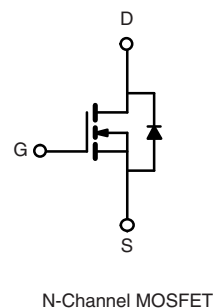
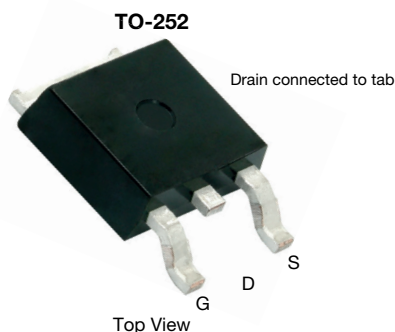
PRODUCT SUMMARY ^d

| | |
|--|--------|
| V _{DS} (V) | 60 |
| R _{DS(on)} (Ω) at V _{GS} = 10 V | 0.042 |
| R _{DS(on)} (Ω) at V _{GS} = 4.5 V | 0.060 |
| I _D (A) | 15 |
| Configuration | Single |
| Package | TO-252 |

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Package with low thermal resistance
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912

AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

| ABSOLUTE MAXIMUM RATINGS (V _C = 25 °C, unless otherwise noted) | | | | |
|---|-------------------------------------|-----------------------------------|-------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | V _{DS} | 60 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | |
| Continuous Drain Current | T _C = 25 °C ^a | I _D | 15 | A |
| | T _C = 125 °C | | 10 | |
| Continuous Source Current (Diode Conduction) ^a | | I _S | 15 | |
| Pulsed Drain Current ^b | | I _{DM} | 50 | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 18 | |
| Single Pulse Avalanche Energy | | E _{AS} | 16.2 | mJ |
| Maximum Power Dissipation ^b | T _C = 25 °C | P _D | 37 | W |
| | T _C = 125 °C | | 11 | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +175 | °C |

THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | LIMIT | UNIT |
|--------------------------|-------------------|-------|------|
| Junction-to-Ambient | R _{thJA} | 50 | °C/W |
| Junction-to-Case (Drain) | R _{thJC} | 4 | |

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).



| SPECIFICATIONS (T _C = 25 °C, unless otherwise noted) | | | | | | | |
|---|---------------------|--|---|------|-------|-------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | | 60 | - | - | V |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | | 1.5 | 2 | 2.5 | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 60 V | - | - | 1 | μA |
| | | V _{GS} = 0 V | V _{DS} = 60 V, T _J = 125 °C | - | - | 50 | |
| | | V _{GS} = 0 V | V _{DS} = 60 V, T _J = 175 °C | - | - | 150 | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | V _{DS} ≥ 5 V | 30 | - | - | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V | I _D = 10 A | - | 0.036 | 0.042 | Ω |
| | | V _{GS} = 10 V | I _D = 10 A, T _J = 125 °C | - | - | 0.075 | |
| | | V _{GS} = 10 V | I _D = 10 A, T _J = 175 °C | - | - | 0.090 | |
| | | V _{GS} = 4.5 V | I _D = 10 A, T _J = 125 °C | - | 0.092 | - | |
| | | V _{GS} = 4.5 V | I _D = 10 A, T _J = 175 °C | - | 0.110 | - | |
| | | V _{GS} = 4.5 V | I _D = 10 A | - | 0.048 | 0.060 | |
| Forward Transconductance ^b | g _{fs} | V _{DS} = 15 V, I _D = 6 A | | - | 11 | - | S |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | V _{GS} = 0 V | V _{DS} = 25 V, f = 1 MHz | - | 425 | 535 | pF |
| Output Capacitance | C _{oss} | | | - | 95 | 120 | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 40 | 50 | |
| Total Gate Charge ^c | Q _g | V _{GS} = 10 V | V _{DS} = 30 V, I _D = 15 A | - | 9.5 | 15 | nC |
| Gate-Source Charge ^c | Q _{gs} | | | - | 1.7 | - | |
| Gate-Drain Charge ^c | Q _{gd} | | | - | 2.5 | - | |
| Gate Resistance | R _g | f = 1 MHz | | 1.2 | 2.5 | 5.4 | Ω |
| Turn-On Delay Time ^c | t _{d(on)} | V _{DD} = 30 V, R _L = 2 Ω I _D ≡ 15 A, V _{GEN} = 10 V, R _g = 1 Ω | | - | 5 | 8 | ns |
| Rise Time ^c | t _r | | | - | 10 | 15 | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 13 | 20 | |
| Fall Time ^c | t _f | | | - | 8 | 12 | |
| Source-Drain Diode Ratings and Characteristics ^b | | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 50 | A |
| Forward Voltage | V _{SD} | I _F = 10 A, V _{GS} = 0 V | | - | 0.9 | 1.2 | V |
| Reverse Recovery Time | t _{rr} | I _F = 15 A, dI/dt = 100 A/μs | | - | 29 | 60 | ns |

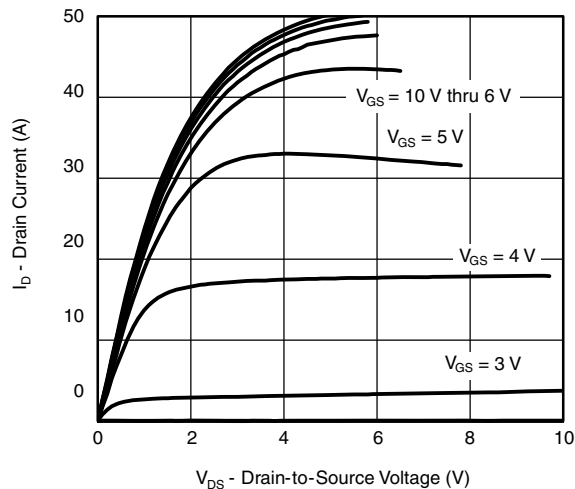
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

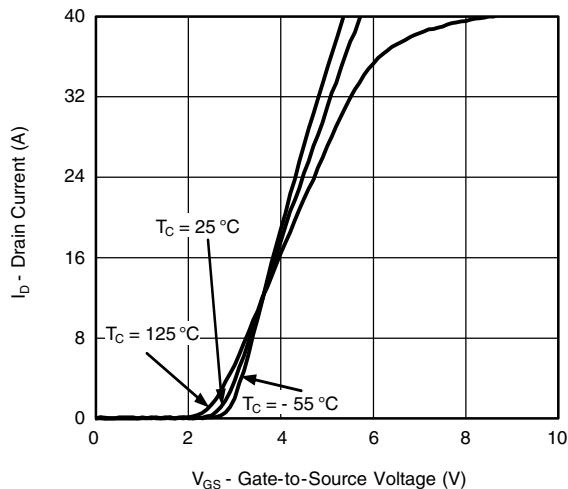
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



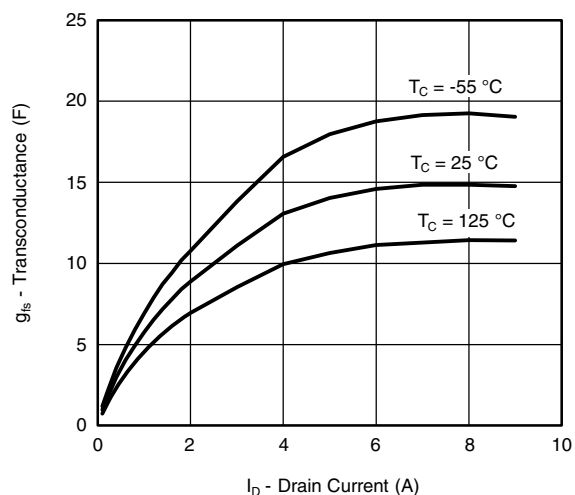
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



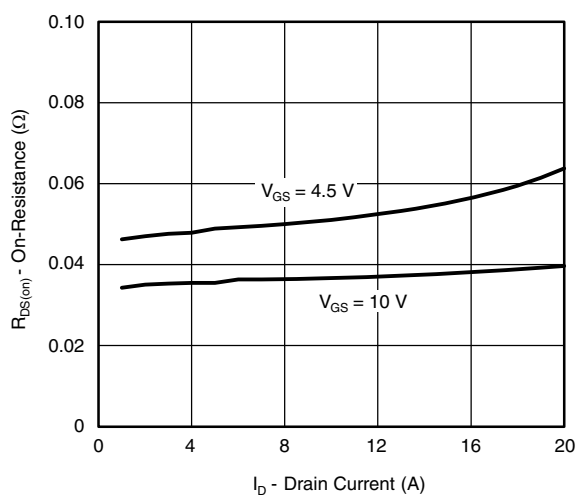
Output Characteristics



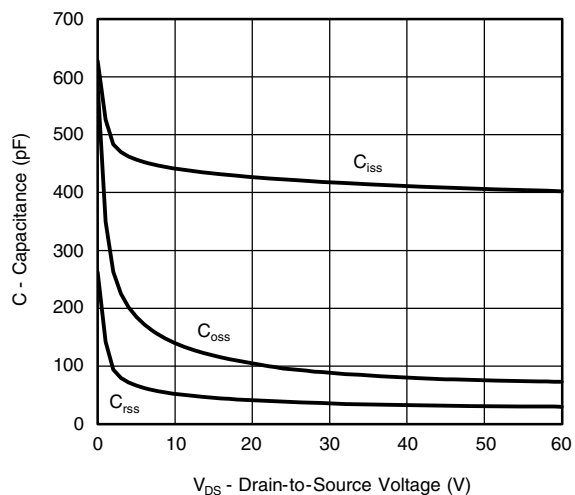
Transfer Characteristics



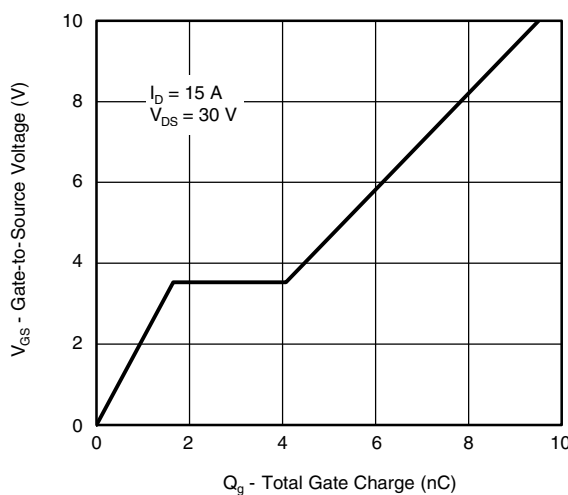
Transconductance



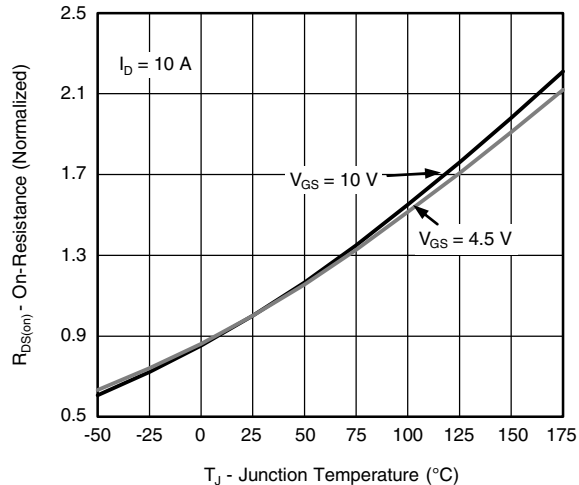
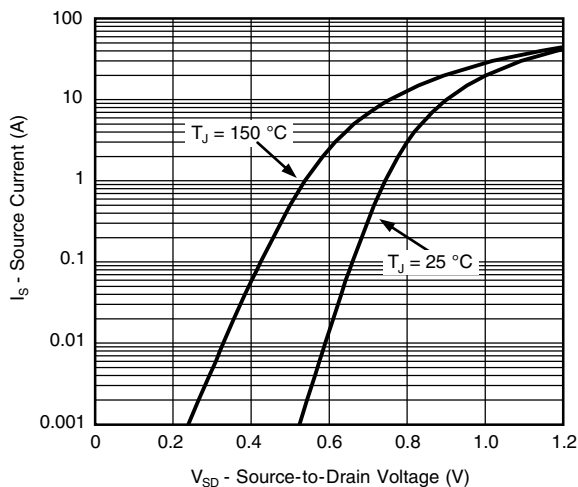
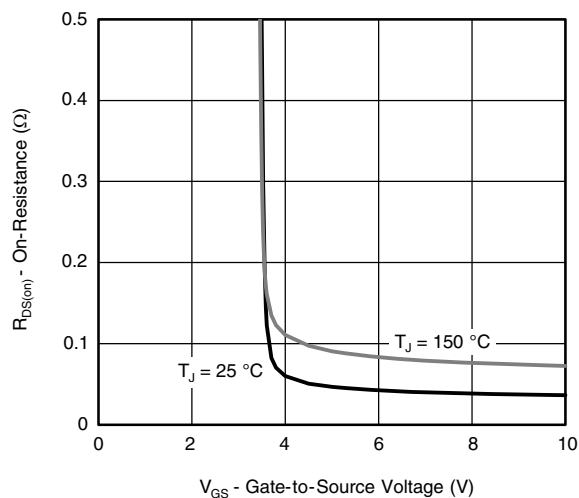
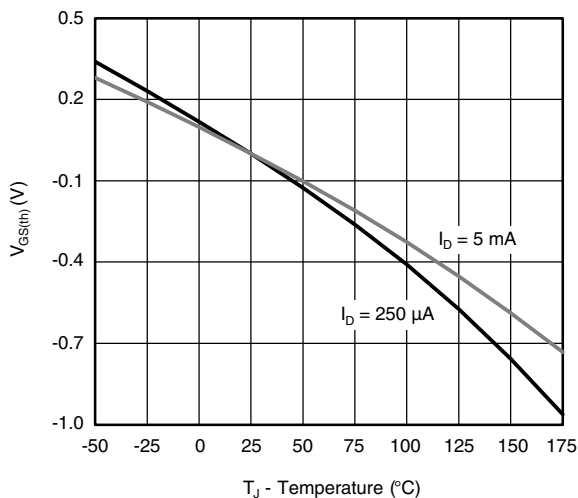
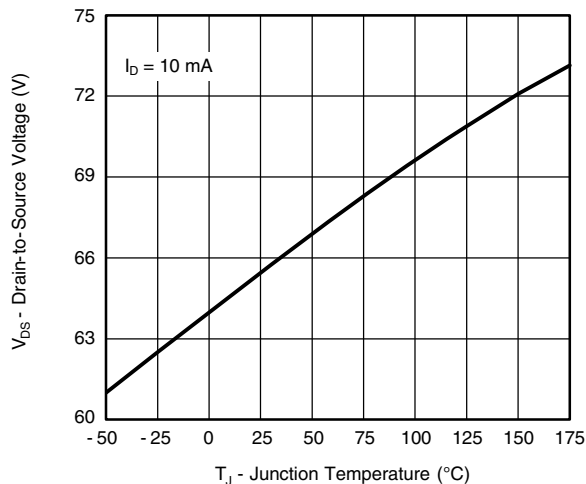
On-Resistance vs. Drain Current



Capacitance

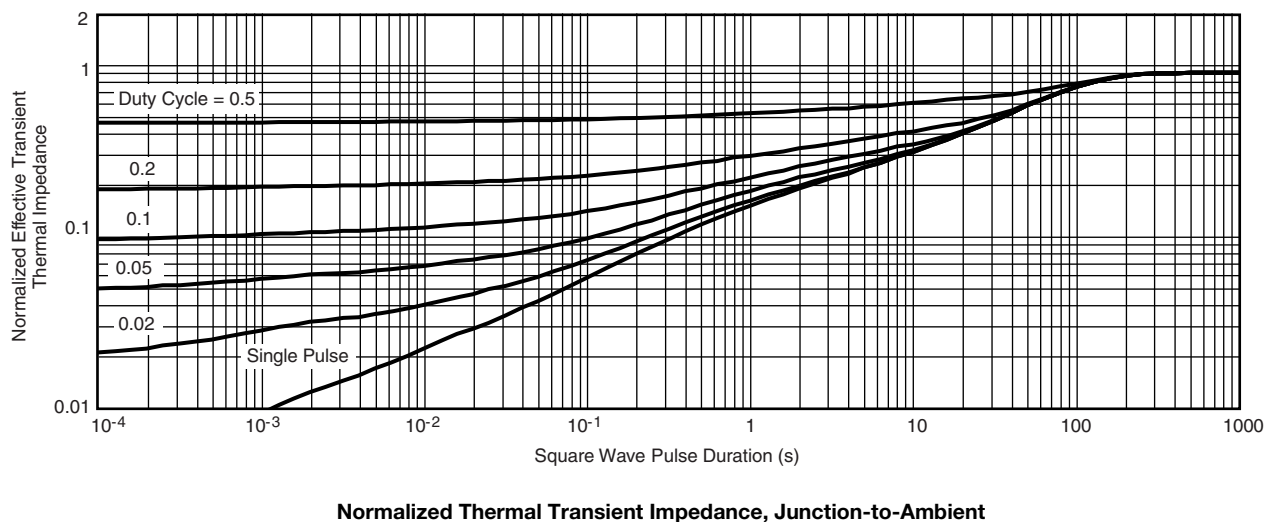
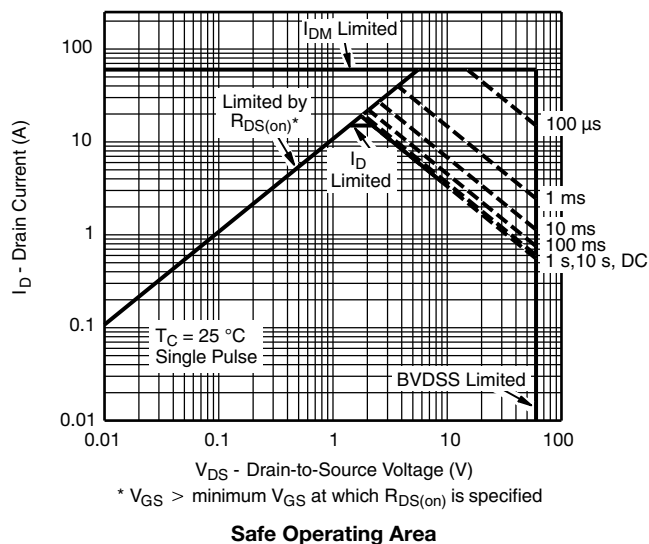


Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

On-Resistance vs. Junction Temperature

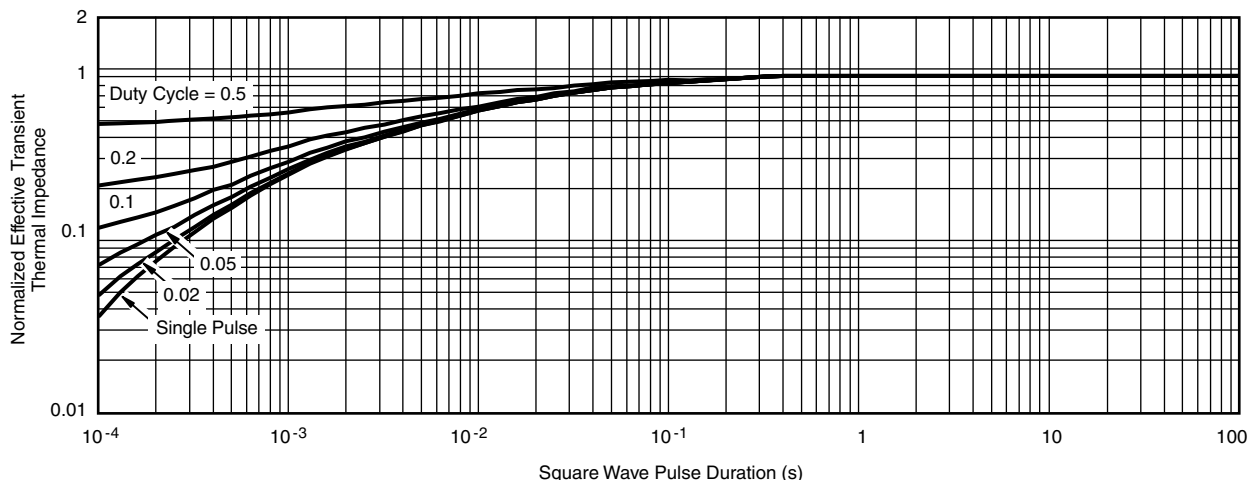


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68880.



| REVISION HISTORY ^a | | |
|-------------------------------|-----------|--|
| REVISION | DATE | DESCRIPTION OF CHANGE |
| G | 04-Aug-15 | • Revised R _g minimum limit |

Note

a. As of April 2014

**DPAK / TO-252 and Reverse DPAK**

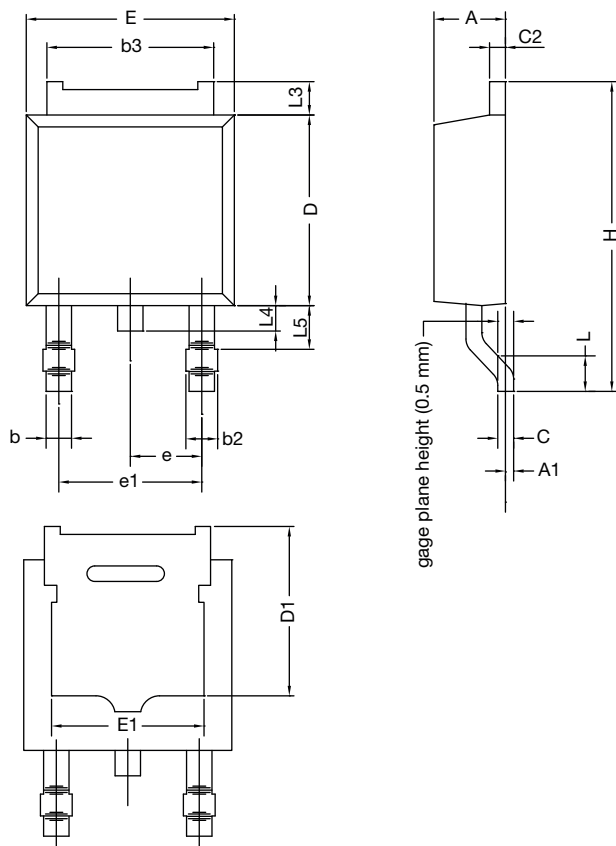
Ordering codes for the SQ rugged series power MOSFETs in the DPAK / TO-252 and Reverse DPAK packages:

| DATASHEET PART NUMBER | OLD ORDERING CODE ^a | NEW ORDERING CODE |
|-----------------------|--------------------------------|--------------------|
| SQD07N25-350H | SQD07N25-350H-GE3 | SQD07N25-350H_GE3 |
| SQD100N03-3m2L | SQD100N03-3M2L-GE3 | SQD100N03-3M2L_GE3 |
| SQD100N03-3m4 | SQD100N03-3M4-GE3 | SQD100N03-3M4_GE3 |
| SQD100N04-3m6 | SQD100N04-3M6-GE3 | SQD100N04-3M6_GE3 |
| SQD100N04-3m6L | SQD100N04-3M6L-GE3 | SQD100N04-3M6L_GE3 |
| SQD10N30-330H | SQD10N30-330H-GE3 | SQD10N30-330H_GE3 |
| SQD15N06-42L | SQD15N06-42L-GE3 | SQD15N06-42L_GE3 |
| SQD19P06-60L | SQD19P06-60L-GE3 | SQD19P06-60L_GE3 |
| SQD23N06-31L | SQD23N06-31L-GE3 | SQD23N06-31L_GE3 |
| SQD25N06-22L | SQD25N06-22L-GE3 | SQD25N06-22L_GE3 |
| SQD25N15-52 | SQD25N15-52-GE3 | SQD25N15-52_GE3 |
| SQD30N05-20L | SQD30N05-20L-GE3 | SQD30N05-20L_GE3 |
| SQD40N06-14L | SQD40N06-14L-GE3 | SQD40N06-14L_GE3 |
| SQD40N10-25 | SQD40N10-25-GE3 | SQD40N10-25_GE3 |
| SQD40P10-40L | SQD40P10-40L-GE3 | SQD40P10-40L_GE3 |
| SQD45P03-12 | SQD45P03-12-GE3 | SQD45P03-12_GE3 |
| SQD50N04-5m6 | SQD50N04-5M6-GE3 | SQD50N04-5M6_GE3 |
| SQD50N05-11L | SQD50N05-11L-GE3 | SQD50N05-11L_GE3 |
| SQD50N06-09L | SQD50N06-09L-GE3 | SQD50N06-09L_GE3 |
| SQD50N10-8m9L | SQD50N10-8M9L-GE3 | SQD50N10-8M9L_GE3 |
| SQD50P03-07 | SQD50P03-07-GE3 | SQD50P03-07_GE3 |
| SQD50P04-13L | SQD50P04-13L-GE3 | SQD50P04-13L_GE3 |
| SQD50P06-15L | SQD50P06-15L-GE3 | SQD50P06-15L_GE3 |
| SQD50P08-25L | SQD50P08-25L-GE3 | SQD50P08-25L_GE3 |
| SQD50P08-28 | SQD50P08-28-GE3 | SQD50P08-28_GE3 |
| SQD90P04-9m4L | SQD90P04-9M4L-GE3 | SQD90P04-9M4L_GE3 |
| SQD97N06-6m3L | SQD97N06-6M3L-GE3 | SQD97N06-6M3L_GE3 |
| SQR40N10-25 | SQR40N10-25-GE3 | SQR40N10-25_GE3 |
| SQR50N04-3m8 | SQR50N04-3M8-GE3 | SQR50N04-3M8_GE3 |

Note

a. Old ordering code is obsolete and no longer valid for new orders

TO-252AA Case Outline

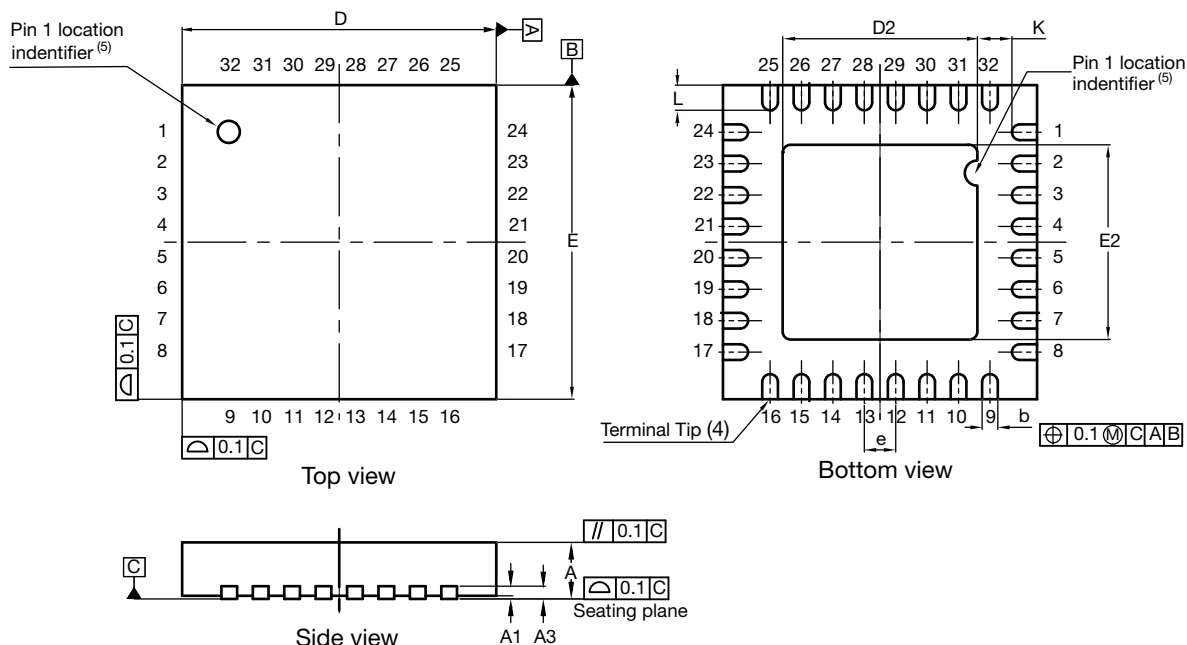


| DIM. | MILLIMETERS | | INCHES | |
|--|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 2.18 | 2.38 | 0.086 | 0.094 |
| A1 | - | 0.127 | - | 0.005 |
| b | 0.64 | 0.88 | 0.025 | 0.035 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 |
| C | 0.46 | 0.61 | 0.018 | 0.024 |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 4.10 | - | 0.161 | - |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| H | 9.40 | 10.41 | 0.370 | 0.410 |
| e | 2.28 BSC | | 0.090 BSC | |
| e1 | 4.56 BSC | | 0.180 BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 |
| L4 | - | 1.02 | - | 0.040 |
| L5 | 1.01 | 1.52 | 0.040 | 0.060 |
| ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019 | | | | |

Note

- Dimension L3 is for reference only.

QFN32 5 x 5 Case Outline



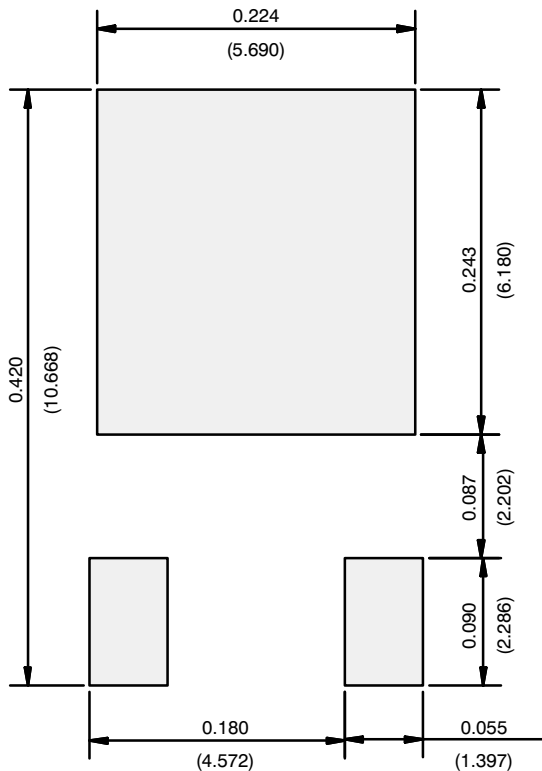
| DIM. | MILLIMETERS | | | INCHES | | |
|-------------------|-------------|------|------|------------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.75 | 0.85 | 0.95 | 0.029 | 0.033 | 0.037 |
| A1 | 0.00 | - | 0.05 | 0.000 | - | 0.002 |
| A3 | 0.20 ref. | | | 0.008 ref. | | |
| b | 0.18 | 0.25 | 0.30 | 0.007 | 0.010 | 0.012 |
| D | 5.00 BSC | | | 0.197 BSC | | |
| D2 | 3.00 | 3.10 | 3.20 | 0.118 | 0.122 | 0.126 |
| e | 0.50 BSC | | | 0.020 BSC | | |
| E | 5.00 BSC | | | 0.197 BSC | | |
| E2 | 3.00 | 3.10 | 3.20 | 0.118 | 0.122 | 0.126 |
| K | 0.20 | - | - | 0.008 | - | - |
| L | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 |
| N ⁽³⁾ | 32 | | | 32 | | |
| Nd ⁽³⁾ | 8 | | | 8 | | |
| Ne ⁽³⁾ | 8 | | | 8 | | |

Notes

- (1) Use millimeters as the primary measurement
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994
- (3) N is the number of terminals,
Nd is the number of terminals in X-direction and
Ne is the number of terminals in Y-direction.
- (4) Dimension b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip
- (5) The pin #1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- (6) Package warpage max. 0.05 mm

S14-2079-Rev. A, 20-Oct-14
DWG: 6027

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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